

High-speed Switching Transistor (60V, 5A)

2SC5103 / 2SC5525

● Features

- 1) Low $V_{CE(sat)}$ (Typ. 0.15V at $I_C / I_B = 3 / 0.15A$)
- 2) High speed switching (t_f : Typ. 0.1 μs at $I_C = 3A$)
- 3) Wide SOA. (safe operating area)
- 4) Complements the 2SA1952 / 2SA2006.

● **Absolute maximum ratings** (Ta = 25°C)

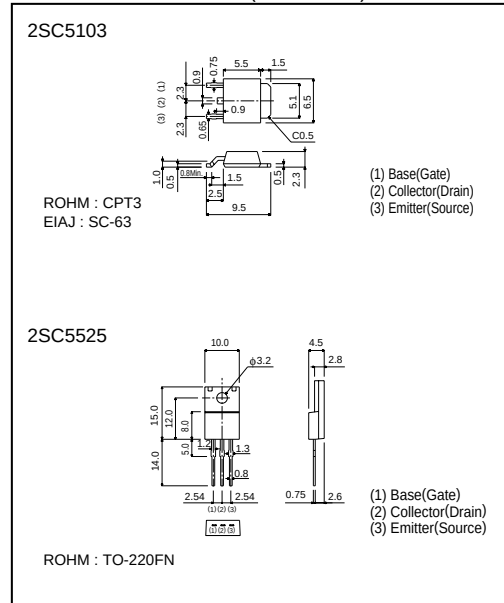
Parameter		Symbol	Limits	Unit
Collector-base voltage		V _{CB0}	100	V
Collector-emitter voltage		V _{CE0}	60	V
Emitter-base voltage		V _{EB0}	5	V
Collector current		I _C	5	A(DC)
			10	A(Pulse) ★
Collector power dissipation	2SC5103	P _C	1	W
			10	W(T _C =25°C)
	2SC5525		2	W
			25	W(T _C =25°C)
Junction temperature		T _J	150	°C
Storage temperature		T _{stg}	-55 ~ +150	°C

*Single pulse Pw=100ms

● Packaging specifications and h_{FE}

Type	2SC5103	2SC5525
Package	CPT3	TO-220FN
h _{FE}	PQ	EF
Code	TL	—
Basic ordering unit (pieces)	2500	500

●External dimensions (Units : mm)



●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	100	—	—	V	$I_C = 50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	60	—	—	V	$I_C = 1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E = 50\mu A$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 100V$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	0.15	0.3	V	$I_C/I_B = 3A/0.15A$ *
		—	—	0.5	V	$I_C/I_B = 4A/0.2A$ *
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	1.2	V	$I_C/I_B = 3A/0.15A$ *
		—	—	1.5	V	$I_C/I_B = 4A/0.2A$ *
DC current transfer ratio	2SC5103	h_{FE}	82	—	—	$V_{CE}/I_C = 2V/1A$
	2SC5525		100	—	320	
Transition frequency	f_T	—	120	—	MHz	$V_{CB} = 10V, I_E = 0.5A, f = 30MHz$ *
Output capacitance	C_{ob}	—	80	—	pF	$V_{CE} = 10V, I_E = 0A, f = 1MHz$
Turn-on time	t_{on}	—	—	0.3	μs	$I_C = 3A, R_L = 10\Omega$
Storage time	t_{stg}	—	—	1.5	μs	$I_{B1} = -I_{B2} = 0.15A$
Fall time	t_f	—	0.1	0.3	μs	$V_{CC} \approx 30V$

* Measured using pulse current.